

SemDex Mf 201

This most cost-effective fully manual system permits spot-to-spot measurements of (substrate-) layer thicknesses. Wafers up to 8" can be evaluated.



Applications:

- (Substrate-) layer thickness ($t > 3 \mu\text{m}$)
- Bow/ warp
- Flatness (SBIR, SFQR etc.)
- Topography (Mini-bumps)
- Roughness ($R_a > 0.1 \mu\text{m}$)

Substrat-Materials:

Materials:

- Silizium
- GaAs
- CdTe
- Glass and others

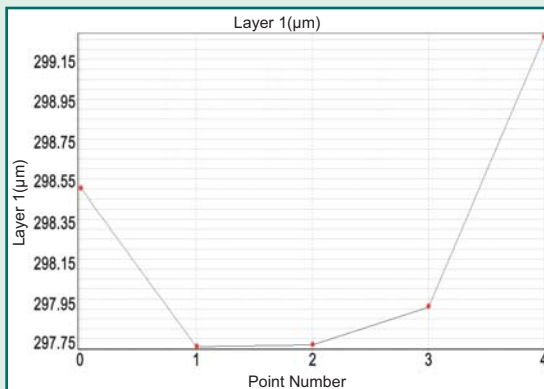
Thin Layer-Materials:

- SOI
- Polyamide
- Photoresist (spin coating)

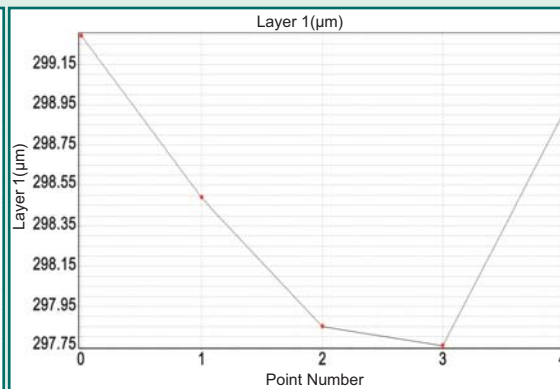
Your benefits:

- † Contactless measurements in reflection mode
- † Very high acquisition rates of up to 16 kHz
- † Repeatabilities better than 50 nm
- † Near-edge exclusion or fine structures due to small spot size (20 or 5 μm)
- † Substrate thickness measurements not affected by tape, bumps etc.

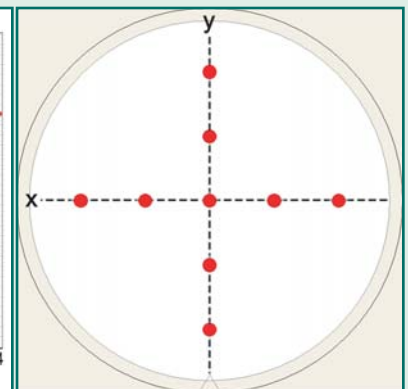
- † All different materials measurable: Silicon, InGaAs, InP, SiC, TFT-Glass, Ceramics, Tape, Photoresist, etc.
- † (Multiple-) layer thicknesses, bow/ warp and flatness in one scan available
- † Negligible shadowing at steep trenches (bumps)
- † Automatic beam refocussing at various working heights (multiple chuck)



Measured data in x-direction



Measured data in y-direction



Measured points